


SANYO Semiconductors

DATA SHEET

CPH5846

MOSFET : P-Channel Silicon MOSFET

SBD : Schottky Barrier Diode

General-Purpose Switching Device Applications

Features

- Composite type with a P-Channel Silicon MOSFET (MCH3309) and a Schottky Barrier Diode (SS10015M) contained in one package facilitating high-density mounting.

[MOSFET]

- Low ON-resistance.
- Ultrahigh-speed switching.
- Low voltage drive.

[SBD]

- Short reverse recovery time.
- Low forward voltage.

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
[MOSFET]				
Drain-to-Source Voltage	V _{DSS}		-20	V
Gate-to-Source Voltage	V _{GSS}		±10	V
Drain Current (DC)	I _D		-1.5	A
Drain Current (Pulse)	I _{DP}	PW≤10μs, duty cycle≤1%	-6.0	A
Allowable Power Dissipation	P _D	Mounted on a ceramic board (900mm ² ×0.8mm) 1unit	0.9	W
Channel Temperature	T _{ch}		150	°C
Storage Temperature	T _{stg}		-55 to +125	°C
[SBD]				
Repetitive Peak Reverse Voltage	V _{RSM}		15	V
Nonrepetitive Peak Reverse Surge Voltage	V _{RSM}		15	V
Average Output Current	I _O		1	A
Surge Forward Current	I _{FSM}	50Hz sine wave, 1 cycle	3	A
Junction Temperature	T _j		-55 to +125	°C
Storage Temperature	T _{stg}		-55 to +125	°C

Marking : XY

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CPH5846

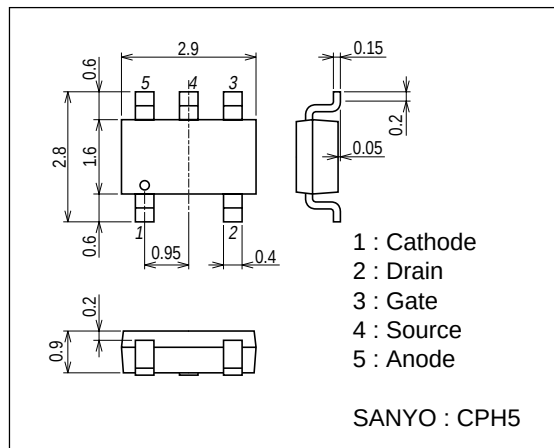
Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
[MOSFET]						
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=-1mA, VGS=0V	-20			V
Zero-Gate Voltage Drain Current	IDSS	VDS=-20V, VGS=0V			-1	μA
Gate-to-Source Leakage Current	IGSS	VGS=±8V, VDS=0V			±10	μA
Cutoff Voltage	VGS(off)	VDS=-10V, ID=-1mA	-0.4		-1.3	V
Forward Transfer Admittance	yfs	VDS=-10V, ID=-800mA	1.3	2.3		S
Static Drain-to-Source On-State Resistance	RDS(on)1	ID=-800mA, VGS=-4V		180	235	mΩ
	RDS(on)2	ID=-400mA, VGS=-2.5V		240	340	mΩ
	RDS(on)3	ID=-70mA, VGS=-1.8V		350	600	mΩ
Input Capacitance	Ciss	VDS=-10V, f=1MHz		290		pF
Output Capacitance	Coss	VDS=-10V, f=1MHz		40		pF
Reverse Transfer Capacitance	Crss	VDS=-10V, f=1MHz		25		pF
Turn-ON Delay Time	td(on)	See specified Test Circuit.		10		ns
Rise Time	tr	See specified Test Circuit.		35		ns
Turn-OFF Delay Time	td(off)	See specified Test Circuit.		32		ns
Fall Time	tf	See specified Test Circuit.		27		ns
Total Gate Charge	Qg	VDS=-10V, VGS=-4V, ID=-1.5A		3.2		nC
Gate-to-Source Charge	Qgs	VDS=-10V, VGS=-4V, ID=-1.5A		0.8		nC
Gate-to-Drain "Miller" Charge	Qgd	VDS=-10V, VGS=-4V, ID=-1.5A		0.6		nC
Diode Forward Voltage	VSD	IS=-1.5A, VGS=0V		-0.87	-1.2	V
[SBD]						
Reverse Voltage	VR	IR=0.5mA	15			V
Forward Voltage	VF1	IF=0.3A		0.31	0.34	V
	VF2	IF=0.5A		0.34	0.37	V
Reverse Current	IR	VR=6V			90	μA
Interterminal Capacitance	C	VR=10V, f=1MHZ, 1 cycle		20		pF
Reverse Recovery Time	trr	IF=IR=100mA, See specified Test Circuit.			10	ns

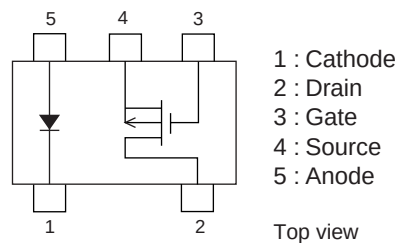
Package Dimensions

unit : mm (typ)

7017A-005

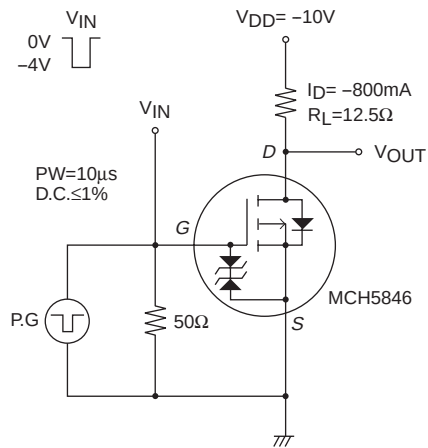


Electrical Connection

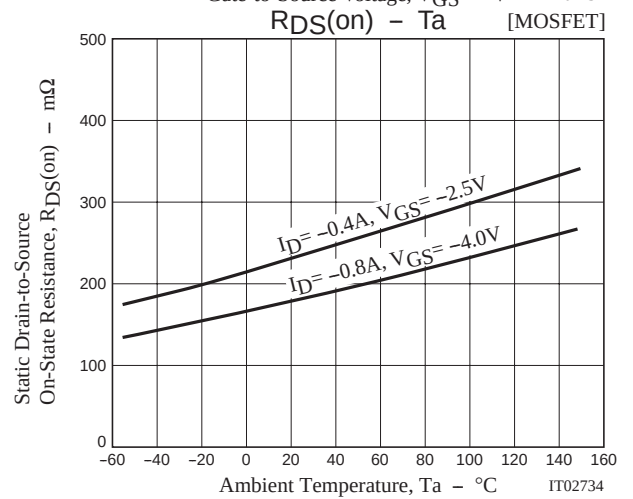
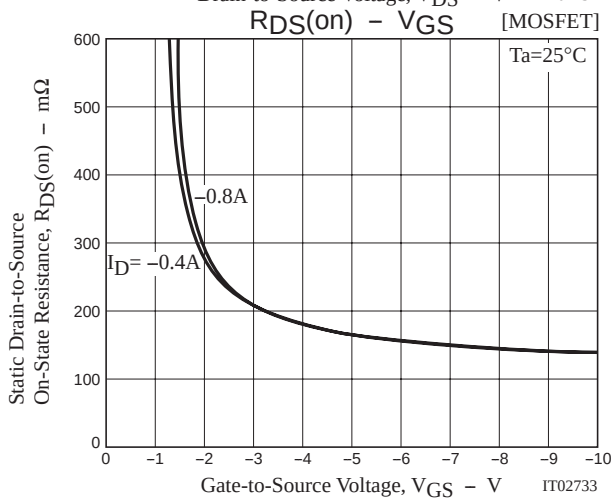
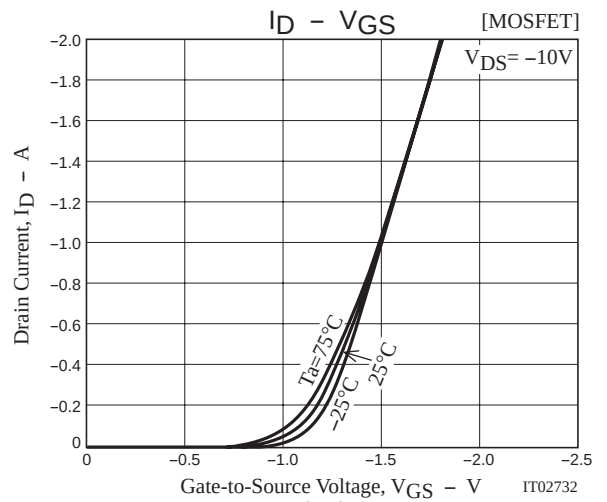
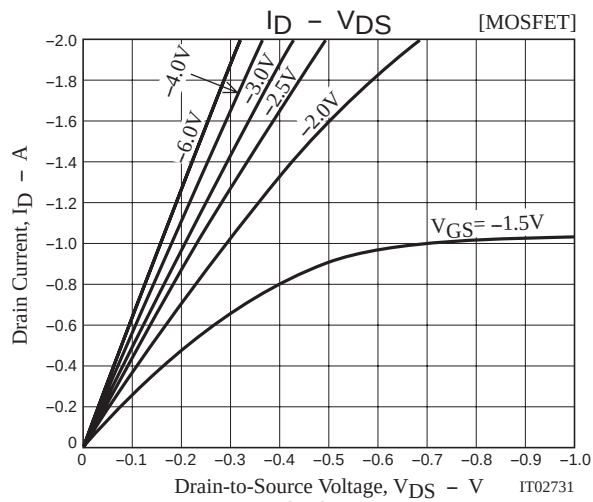
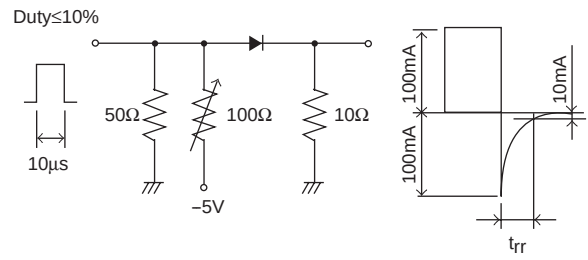


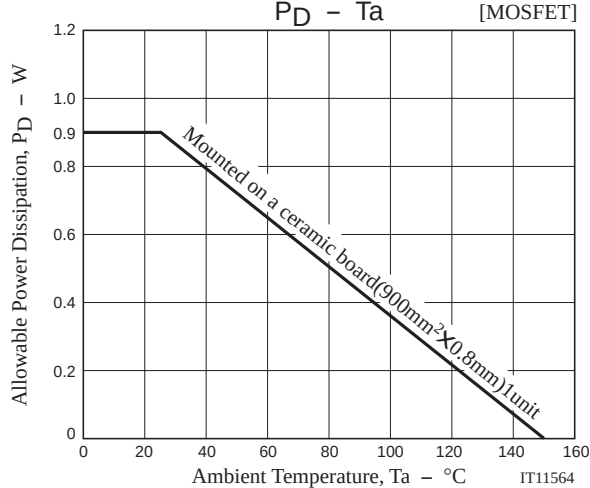
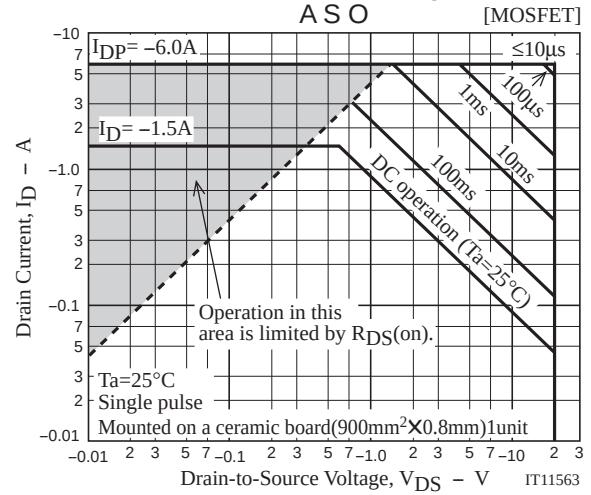
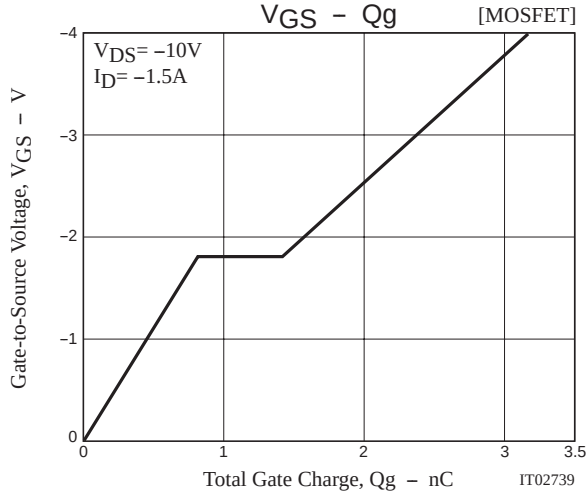
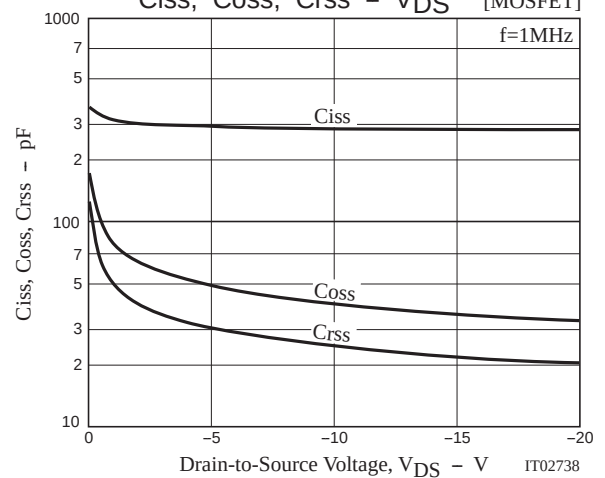
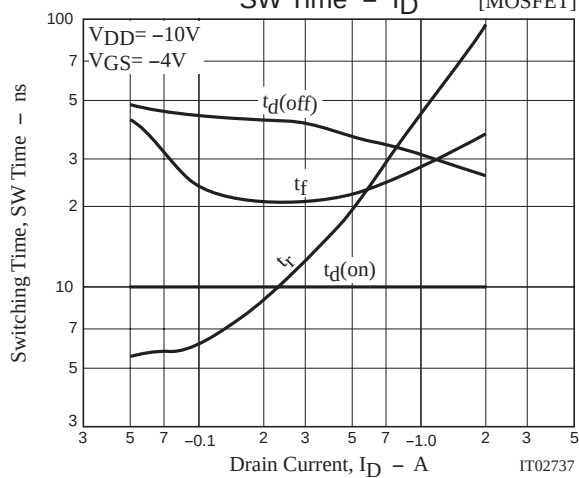
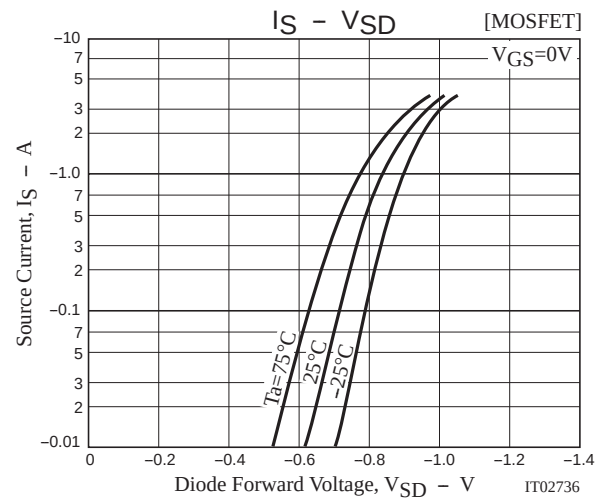
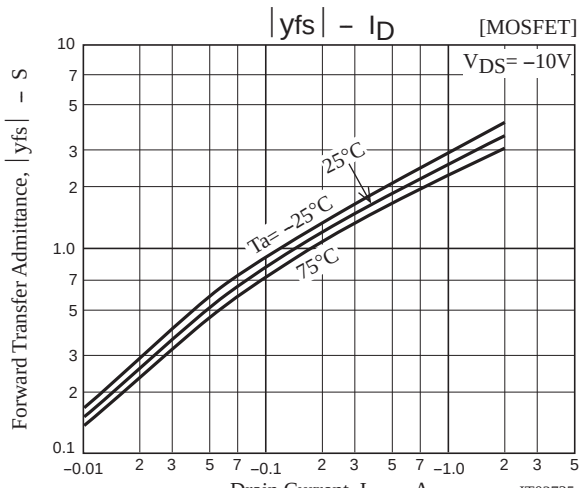
Switching Time Test Circuit

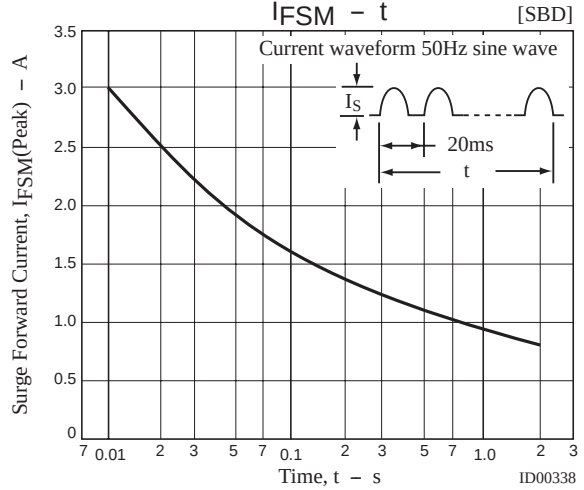
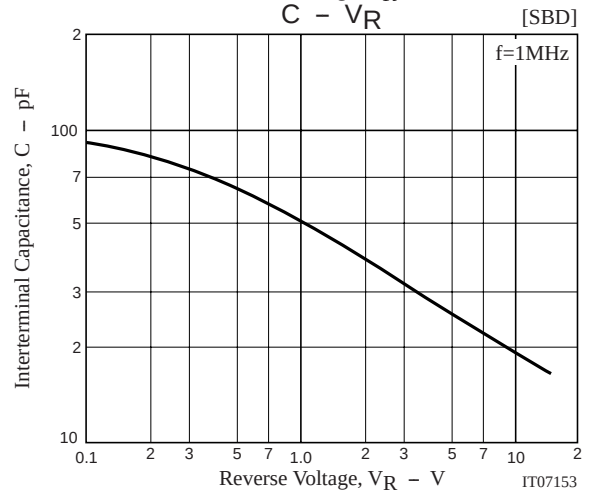
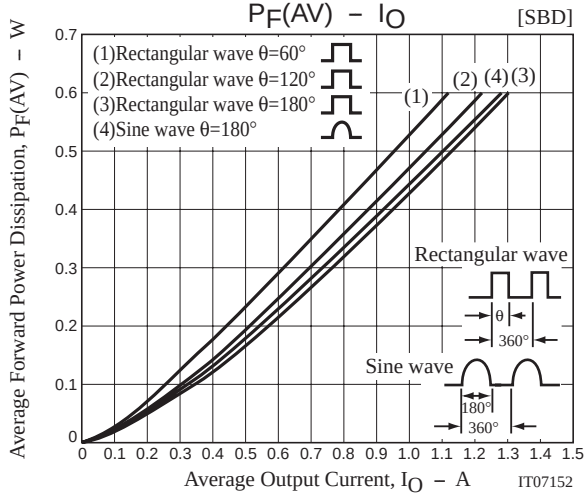
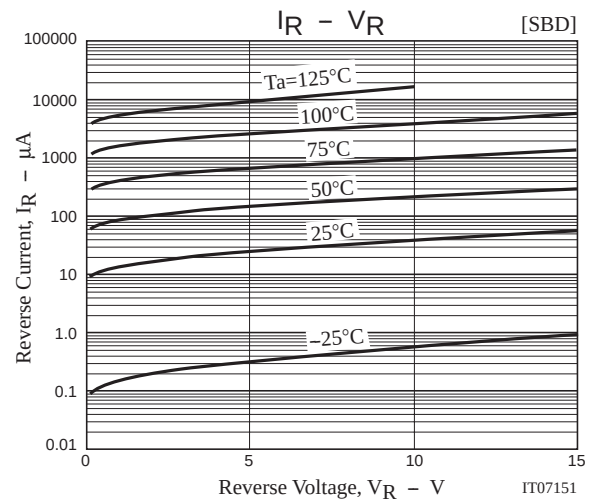
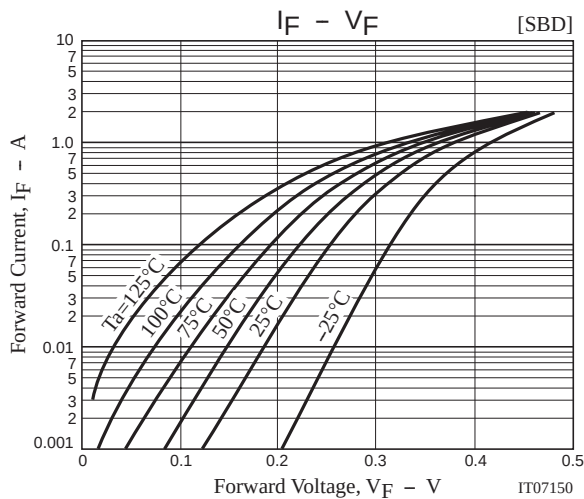
[MOSFET]

 t_{rr} Test Circuit

[SBD]







Note on usage : Since the CPH5846 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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